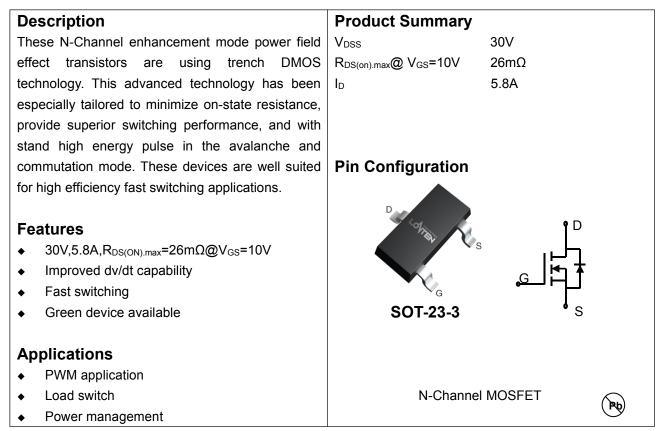


Lonten N-channel 30V, 5.8A, 26mΩ Power MOSFET



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Continuous drain current (T _A = 25°C)		5.8	A
Continuous drain current (T _A = 100°C)	ID	3.7	A
Pulsed drain current ¹⁾	Ідм	23.2	A
Gate-Source voltage	V _{GSS}	±12	V
Power Dissipation ($T_A = 25^{\circ}C$)	P _D	1.4	W
Storage Temperature Range	T _{STG}	-55 to +150	°C
Operating Junction Temperature Range	TJ	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R _{0JA}	89	°C/W



Package Marking and Ordering Information

Device		Device Package SOT-23-3		Marking 3400			
LNSA3400							
Electrical Characteristics	S $T_J = 25^{\circ}C$ unles	ss otherwise noted					
Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Static characteristics		1			1	-	
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =250uA	30			V	
Gate threshold voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_D=250$ uA	0.65	1.0	1.35	V	
		V _{DS} =30 V, V _{GS} =0 V, T _J = 25°C			1	μA	
Drain-source leakage current	I _{DSS}	V _{DS} =24 V, V _{GS} =0 V, T _J = 125°C			10	μA	
Gate leakage current, Forward	I _{GSSF}	V _{GS} =12 V, V _{DS} =0 V			100	nA	
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-12 V, V _{DS} =0 V			-100	nA	
		V _{GS} =10 V, I _D =5.8 A		18	26	mΩ	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =4.5 V, I _D =5 A		20	32	mΩ	
		Vgs=2.5V, Id=4A		31	52	mΩ	
Forward transconductance	g fs	V _{DS} =5 V , I _D =5.8A		30		S	
Dynamic characteristics	1			1	I		
Input capacitance	C _{iss}			494		pF	
Output capacitance	Coss	$V_{DS} = 15 V, V_{GS} = 0 V,$		62.4			
Reverse transfer capacitance	C _{rss}	- F = 1MHz		53.7			
Gate resistance	Rg	V _{GS} =0V,V _{DS} =0V,f=1MHz		4.2		mΩ	
Turn-on delay time	t _{d(on)}			7.6			
Rise time	tr	V _{DD} = 15V,V _{GS} =10V, I _D =5.8 A,		113.2		ns	
Turn-off delay time	t _{d(off)}	Rg=10Ω		44.4			
Fall time	t _f			13.6			
Gate charge characteristics							
Gate to source charge	Q _{gs}			3.3			
Gate to drain charge	Q _{gd}	V _{DS} =15V, I _D =5.8A, V _{GS} = 10V		2.1		nC	
Gate charge total	Qg			13.6			
Drain-Source diode characteris	tics and Maxir	num Ratings					
Continuous Source Current	ls				5.8	А	
Pulsed Source Current ²⁾	I _{SM}				23.2	A	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =5.8A, T _J =25℃			1.2	V	

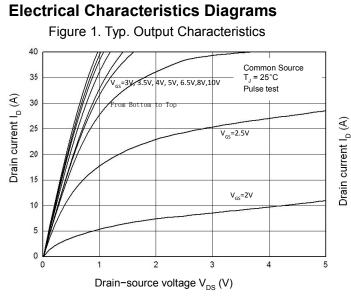
Notes:

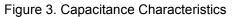
1: Repetitive Rating: Pulse width limited by maximum junction temperature.

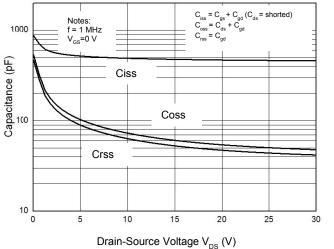
2: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

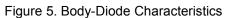


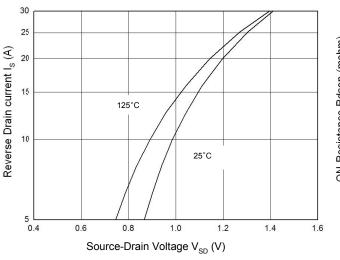
LNSA3400

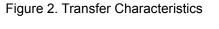


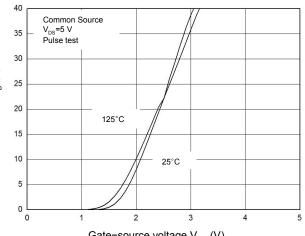






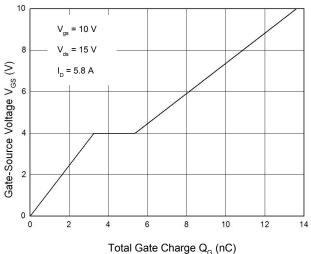






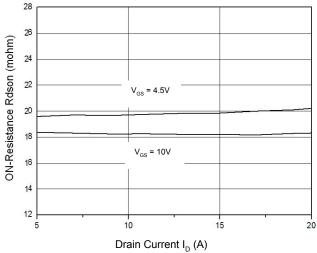
Gate-source voltage V_{GS} (V)





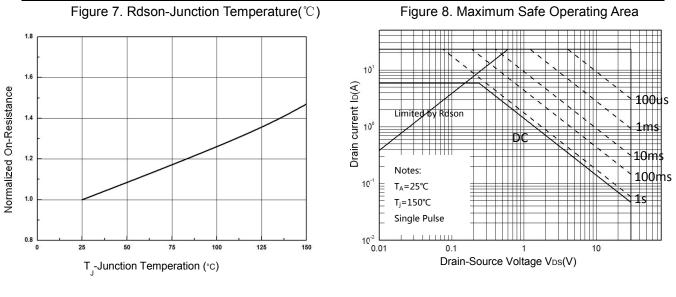
Total Gate Charge Q_{G} (IIC)

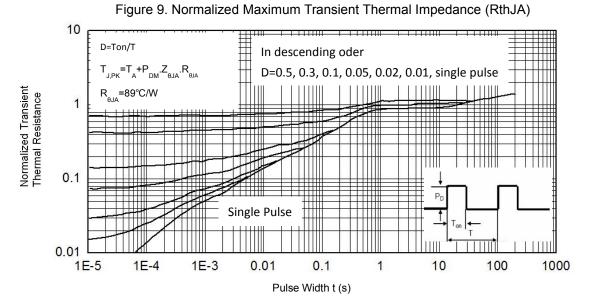






LNSA3400

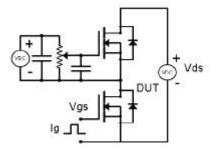






Test Circuit & Waveform

Figure 8. Gate Charge Test Circuit & Waveform



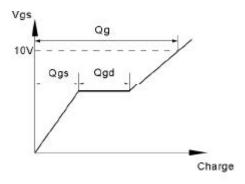


Figure 9. Resistive Switching Test Circuit & Waveforms

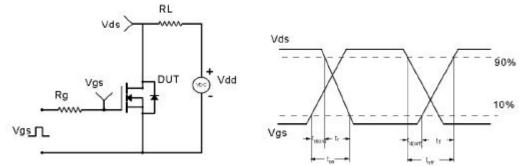
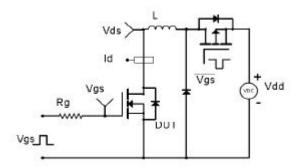


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



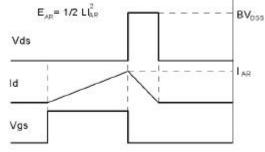
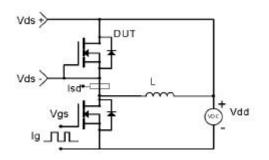
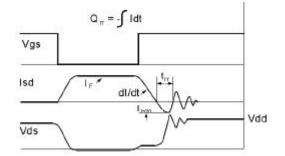


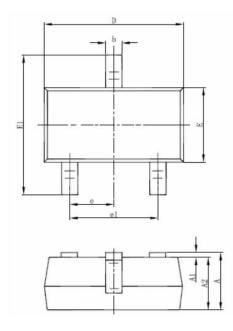
Figure 11. Diode Recovery Circuit & Waveform





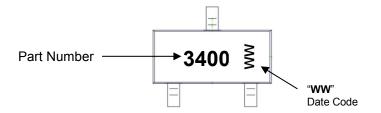


Mechanical Dimensions for SOT-23-3



COMMON DIMENSIONS					
SYMBOL	MILLIMETERS		INCHS		
	MIN	MAX	MIN	MAX	
A	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0.000	0.004	
A2	1.00	1.20	0.039	0.047	
b	0.30	0.50	0.012	0.020	
с	0.04	0.21	0.002	0.008	
D	2.80	3.00	0.110	0.118	
E	1.50	1.70	0.059	0.067	
E1	2.60	3.00	0.102	0.118	
е	0.95 TYP.		0.037 TYP.		
e1	1.90 TYP.		0.075 TYP.		
L	0.25	0.55	0.010	0.022	
θ	0°	8°	0°	8°	

SOT-23-3 Part Marking Information





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